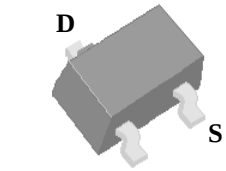
AP2304AGN-HF

Halogen-Free Product

Advanced Power Electronics Corp.

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

- ▼ **Simple Drive Requirement**
- ▼ **Small Package Outline**
- ▼ **Surface Mount Device**
- ▼ **RoHS Compliant**



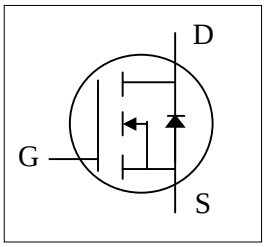
SOT-23

BV_{DSS}	30V
$R_{DS(ON)}$	117mΩ
I_D	2.5A

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-23 package is widely used for all commercial-industrial applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current[3], V_{GS} @ 10V	2.5	A
I_D@T_A=70℃	Continuous Drain Current[3], V_{GS} @ 10V	2	A
I_{DM}	Pulsed Drain Current[1]	10	A
P_D@T_A=25℃	Total Power Dissipation	1.38	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	90	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=2.5A	-	-	117	mΩ
		V_{GS}=4.5V, I_D=2A	-	-	190	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	-	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=2.5A	-	2	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V, V_{GS}=0V	-	-	1	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=24V ,V_{GS}=0V	-	-	10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=2.5A	-	3	5	nC
Q_{gs}	Gate-Source Charge	V_{DS}=24V	-	0.8	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	1.8	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=15V	-	5	-	ns
t_r	Rise Time	I_D=1A	-	9	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω,V_{GS}=10V	-	11	-	ns
t_f	Fall Time	RD=15Ω	-	2	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	120	190	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	62	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	24	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.67	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=1.2A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time[2]	I_S=2A, V_{GS}=0V,	-	24	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	23	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board ; 270℃/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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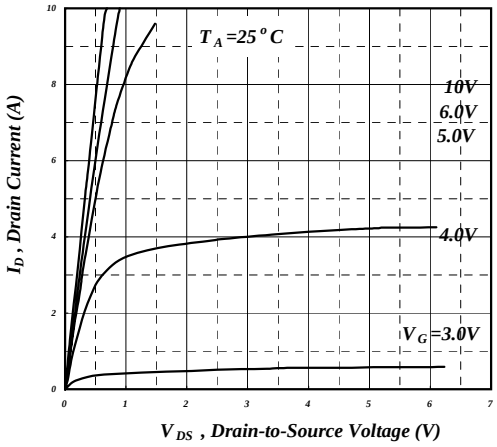


Fig 1. Typical Output Characteristics

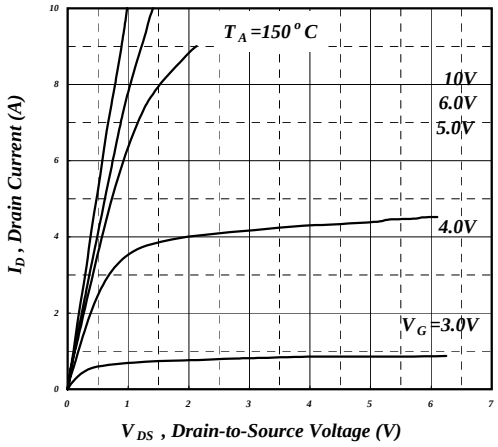


Fig 2. Typical Output Characteristics

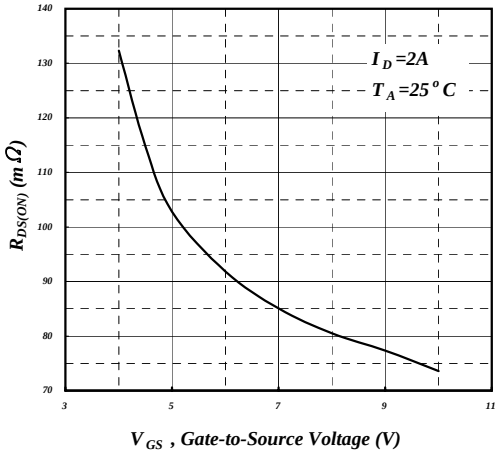


Fig 3. On-Resistance v.s. Gate Voltage

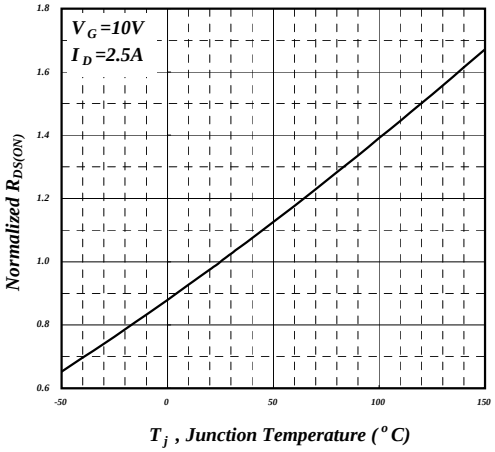


Fig 4. Normalized On-Resistance

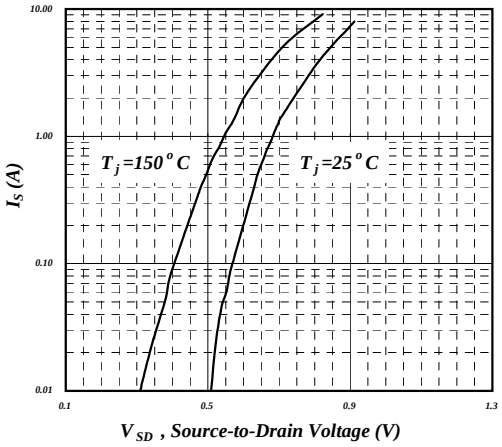


Fig 5. Forward Characteristic of Reverse Diode

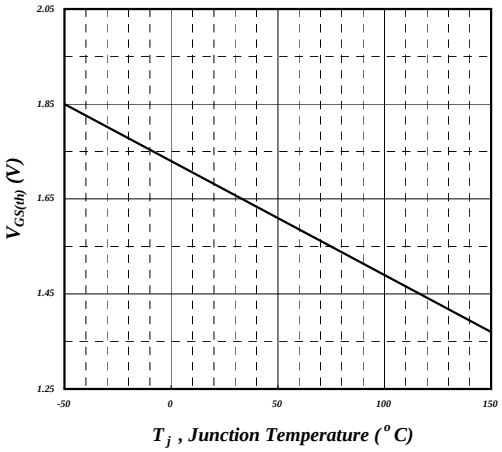


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

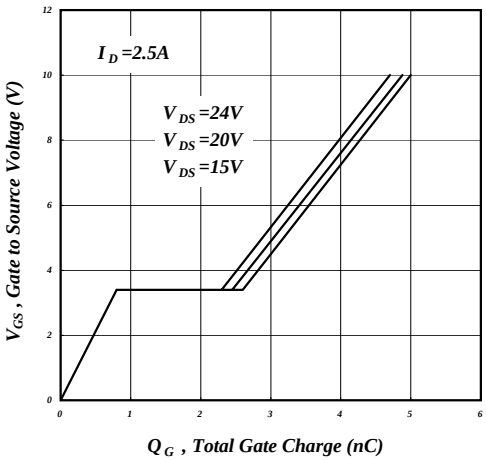


Fig 7. Gate Charge Characteristics

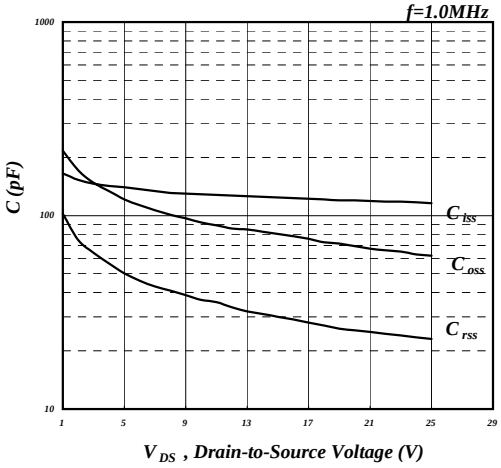


Fig 8. Typical Capacitance Characteristics

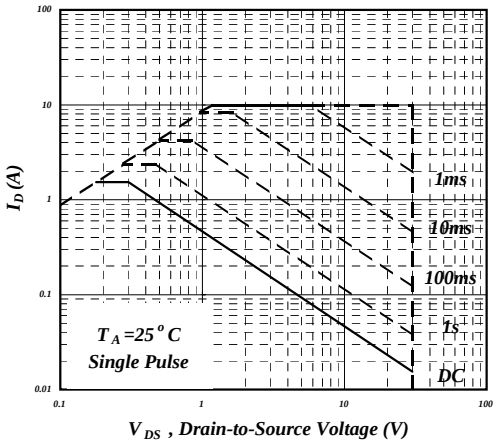


Fig 9. Maximum Safe Operating Area

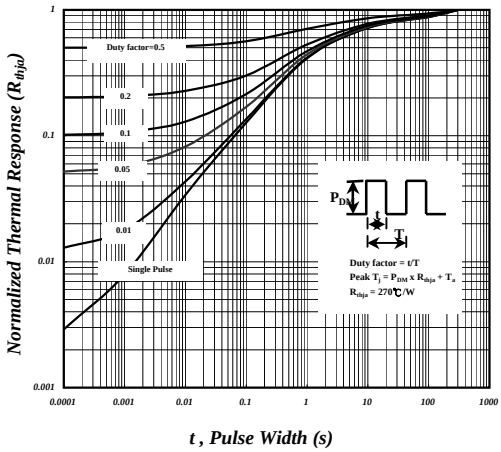


Fig 10. Effective Transient Thermal Impedance

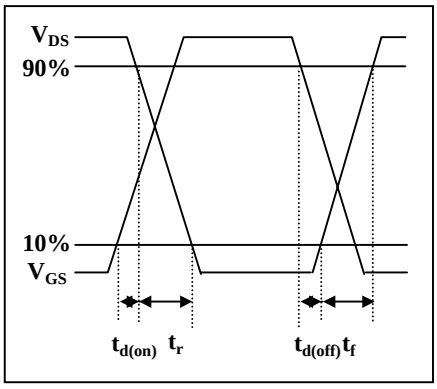


Fig 11. Switching Time Waveform

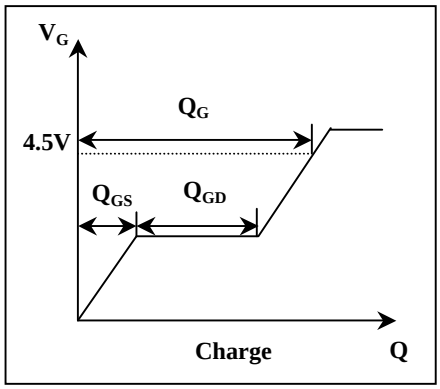


Fig 12. Gate Charge Waveform